# Microwave Device Modeling Exploiting Generalized Space Mapping

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# Outline

Space Mapping (SM) concept (Bandler et al., 1994)

Generalized Space Mapping (GSM) tableau approach for engineering device modeling (*Bandler et al., 2001*)

mathematical formulation of GSM

examples

conclusions





# **Space Mapping Concept**

(Bandler et al., 1994-)







# **Generalized Space Mapping (GSM)**

(Bandler et al., 2001)

GSM is a comprehensive framework to engineering device modeling

GSM exploits the Space Mapping (SM), the Frequency Space Mapping (FSM) (*Bandler et al., 1994*) and the Multiple Space Mapping (MSM) (*Bandler et al., 1998*) concepts to build a new engineering device modeling framework

two cases are considered:

the basic Space Mapping Super Model (SMSM) concept and the basic Frequency-Space Mapping Super Model (FSMSM) concept





# **Space Mapping Super Model (SMSM)**







# **Frequency-Space Mapping Super Model (FSMSM)**







# Multiple Space Mapping (MSM) Concept

MSM for Device Responses (MSMDR)







# Multiple Space Mapping (MSM) Concept

MSM for Frequency Intervals (MSMFI)







# **MSMFI** Algorithm

- Step 1 Initialize *i*=1 and let the frequency interval  $\Omega = [\omega_{\min}, \omega_{\max}]$
- Step 2 Establish a mapping  $P_i$  in the frequency range defined by  $\Omega$
- *Step 3* Assign the mapping  $P_i$  to the frequency interval  $\Omega_i \subset \Omega$  in which the error criteria  $\|\boldsymbol{R}_f \boldsymbol{R}_c\| \leq \varepsilon$  is satisfied
- Step 4 Replace  $\Omega$  by  $\Omega \Omega_i$  and increment *i*
- Step 5 If  $\Omega$  is not empty go to step 2, otherwise stop





## Mathematical Formulation for GSM

the *k*th mapping is given by

$$(\boldsymbol{x}_{ck}, \omega_{ck}) = \boldsymbol{P}_k(\boldsymbol{x}_f, \omega)$$

in matrix form, assuming a linear mapping

$$\begin{bmatrix} \boldsymbol{x}_{ck} \\ \boldsymbol{\omega}_{ck} \end{bmatrix} = \begin{bmatrix} \boldsymbol{c}_k \\ \boldsymbol{\delta}_k \end{bmatrix} + \begin{bmatrix} \boldsymbol{B}_k & \boldsymbol{s}_k \\ \boldsymbol{t}_k^T & \boldsymbol{\sigma}_k \end{bmatrix} \begin{bmatrix} \boldsymbol{x}_f \\ \boldsymbol{\omega} \end{bmatrix}$$

the mapping parameters { $c_k$ ,  $B_k$ ,  $s_k$ ,  $t_k$ ,  $\sigma_k$ ,  $\delta_k$ } can be evaluated by solving the optimization problem

$$\min_{\boldsymbol{c}_k, \boldsymbol{B}_k, \boldsymbol{s}_k, \boldsymbol{t}_k, \boldsymbol{\sigma}_k, \boldsymbol{\delta}_k} \| [\boldsymbol{e}_{k1}^T \quad \boldsymbol{e}_{k2}^T \quad \cdots \quad \boldsymbol{e}_{km}^T]^T \|$$

where *m* is the number of base points selected in the fine model space and  $e_{kj}$  is an error vector given by

$$e_{kj} = R_f(x_f^{(j)}, \omega) - R_c(x_{ck}^{(j)}, \omega_{ck}), \quad j = 1, 2, ..., m$$





#### Mathematical Formulation for GSM (continued)

we impose constraints on the mapping parameters such that they are as close as possible to those corresponding to a unit mapping

the objective function is modified as

$$\min_{\boldsymbol{c}_k,\boldsymbol{B}_k,\boldsymbol{s}_k,\boldsymbol{t}_k,\boldsymbol{\sigma}_k,\boldsymbol{\delta}_k} w_1 \| [\boldsymbol{e}_{k1}^T \quad \boldsymbol{e}_{k2}^T \quad \cdots \quad \boldsymbol{e}_{km}^T]^T \| + w_2 \| \boldsymbol{\beta}_k \|$$

where

$$\boldsymbol{\beta}_{k} = [\boldsymbol{c}_{k}^{T} \ \boldsymbol{s}_{k}^{T} \ \boldsymbol{t}_{k}^{T} \ \Delta \boldsymbol{b}_{k1}^{T} \cdots \Delta \boldsymbol{b}_{kn}^{T} \ \Delta \boldsymbol{\sigma}_{k} \ \boldsymbol{\delta}_{k}]^{T}$$
$$\Delta \boldsymbol{B}_{k} = \boldsymbol{B}_{k} - \boldsymbol{I}$$
$$\Delta \boldsymbol{\sigma}_{k} = \boldsymbol{\sigma}_{k} - 1$$





#### **Selection of the Base Points**

the selection of the base points in the region of interest follows the star distribution (*Bandler et al., 1989*)

according to this distribution the number of base points for a circuit with *n* design parameters is m = 2n + 1







#### An Implementation of SMSM and FSMSM

select *m* base points  $\{x_f^{(j)}, j=1,2,...,m\}$  in the region of interest (star distribution)

for SMSM apply direct optimization to solve

$$\min_{\boldsymbol{c}_k,\boldsymbol{B}_k} w_1 \| [\boldsymbol{e}_{k1}^T \quad \boldsymbol{e}_{k2}^T \quad \cdots \quad \boldsymbol{e}_{km}^T]^T \| + w_2 \| \boldsymbol{\beta}_k \|$$

explicitly setting  $s_k = 0$ ,  $t_k = 0$ ,  $\sigma_k = 1$ ,  $\delta_k = 0$ 

for FSMSM apply direct optimization to solve

$$\min_{\boldsymbol{c}_k,\boldsymbol{B}_k,\boldsymbol{s}_k,\boldsymbol{t}_k,\boldsymbol{\sigma}_k,\boldsymbol{\delta}_k} w_1 \| [\boldsymbol{e}_{k1}^T \quad \boldsymbol{e}_{k2}^T \quad \cdots \quad \boldsymbol{e}_{km}^T]^T \| + w_2 \| \boldsymbol{\beta}_k \|$$





## **Comparison between SMSM and FSMSM**

#### Microstrip Transmission Line



the region of interest

 $10 \text{ mil} \le W \le 30 \text{ mil}$  $40 \text{ mil} \le L \le 60 \text{ mil}$  $10 \text{ mil} \le H \le 20 \text{ mil}$  $8 \le \varepsilon_r \le 10$ 

the frequency range is 20 GHz to 30 GHz

the number of base points is 9 and the number of test points is 50





## **Microstrip Transmission Line**

SMSM and FSMSM mapping parameters for the microstrip transmission line

	SMSM	FSMSM
В	$\begin{bmatrix} 1.015 & -0.002 & -0.007 & -0.022 \\ -0.001 & 0.992 & 0.020 & 0.023 \\ -0.008 & 0.001 & 0.985 & 0.027 \\ 0.009 & -0.004 & 0.044 & 1.028 \end{bmatrix}$	$\begin{bmatrix} 1.026 - 0.005 & 0.006 - 0.021 \\ -0.009 & 0.965 & -0.011 & 0.017 \\ -0.002 & 0.004 & 0.979 & 0.022 \\ 0.019 - 0.001 & 0.020 & 1.025 \end{bmatrix}$
С	$\begin{bmatrix} -0.011 & -0.008 & 0.012 & -0.036 \end{bmatrix}^T$	$\begin{bmatrix} -0.013 & 0.001 & 0.011 & -0.010 \end{bmatrix}^T$
S	<b>0</b> (fixed)	$\begin{bmatrix} -0.006 & 0 & 0.002 & -0.002 \end{bmatrix}^T$
t	<b>0</b> (fixed)	0
σ	1 (fixed)	1.035
$\delta$	0 (fixed)	0.001





# **Microstrip Transmission Line**

the error in  $S_{21}$  at the test points



before applying any modeling technique

applying SMSM







# **Microstrip Right Angle Bend**



the region of interest

 $20 \text{ mil} \le W \le 30 \text{ mil}$  $8 \text{ mil} \le H \le 16 \text{ mil}$  $8 \le \varepsilon_r \le 10$ 

the fine model is analyzed by Sonnet's *em* the "coarse" model is a Jansen empirical model (*Jansen et al.*, 1983) the frequency range is 1 GHz to 41 GHz

the number of base points is 7 and the number of test points is 50





# **Microstrip Right Angle Bend**

the error in  $S_{11}$  at the test points



the error in  $S_{11}$  at the test points applying FSMSM







# Microstrip Right Angle Bend

the error in  $S_{21}$  at the test points



the error in  $S_{21}$  at the test points applying FSMSM









the fine model is analyzed by Sonnet's *em* 

the coarse model is an element of OSA90/hope

the region of interest

 $20 \text{ mil} \le W_1 \le 40 \text{ mil}$  $10 \text{ mil} \le W_2 \le 20 \text{ mil}$  $10 \text{ mil} \le H \le 20 \text{ mil}$  $8 \le \varepsilon_r \le 10$ 

the frequency range is 2 GHz to 40 GHz

the number of base points is 9 and the number of test points is 50





MSM for Device Responses (MSMDR) is developed to enhance the coarse model of the microstrip step junction

	Target responses are {Im[ $S_{11}$ ], Im[ $S_{21}$ ], Im[ $S_{22}$ ],Re[ $S_{21}$ ]}	Target responses are $\{\text{Re}[S_{11}], \text{Re}[S_{22}]\}$
В	$\begin{bmatrix} 0.764 & 0.033 & -0.062 & 0.074 \\ 0.191 & 0.632 & 0.255 & -0.502 \\ -0.023 & 0.116 & 1.485 & 0.018 \\ 0.676 & -0.365 & -0.111 & 0.177 \end{bmatrix}$	3.071 -0.008 -0.010 -0.004   0.008 0.202 0.032 0.004   -0.001 0.001 1.152 0.000   -0.077 -0.118 -0.002 1.241
С	$\begin{bmatrix} 0.002 & -0.002 & 0.002 & -0.006 \end{bmatrix}^T$	$\begin{bmatrix} -0.001 & 0.001 & 0.000 & -0.003 \end{bmatrix}^T$
S	$\begin{bmatrix} -0.003 & 0.004 & -0.001 & -0.002 \end{bmatrix}^T$	0
t	$\begin{bmatrix} -0.001 & 0.000 & -0.005 & 0.000 \end{bmatrix}^T$	$\begin{bmatrix} -0.001 & 0.000 & -0.007 & 0.003 \end{bmatrix}^T$
$\sigma$	1.546	5.729
$\delta$	0.113	0.065





the error in  $S_{11}$  at the test points



the error in  $S_{11}$  at the test points after applying (MSMDR)







the error in  $S_{21}$  at the test points

the error in  $S_{21}$  at the test points after applying (MSMDR)









#### the fine and coarse models







the region of interest

 $15 \text{ mil} \le H \le 25 \text{ mil}$  $2 \text{ mil} \le X \le 10 \text{ mil}$  $15 \text{ mil} \le Y \le 25 \text{ mil}$  $8 \le \varepsilon_r \le 10$ 

the frequency range is 2 GHz to 20 GHz with a step of 2 GHz

the number of base points is 9, the number of test points is 50

the widths W of the input lines track H so that their characteristic impedance is 50 ohm

 $W_1 = W/3$ 

 $W_2$  is suitably constrained





# MSMFI is developed to enhance the accuracy of the coarse model

#### our algorithm determined two intervals: 2-16 GHz and 16-20 GHz

	2 GHz to 16 GHz	16 GHz to 20 GHz
В	$\begin{bmatrix} 1.04 & 0.07 & 0.01 & 0.08 & -0.06 & 0.00 & 0.22 \\ 0.00 & 0.89 & 0.00 & -0.07 & -0.20 & 0.06 & -0.03 \\ -0.00 & 0.07 & 0.99 & 0.04 & -0.12 & 0.01 & -0.06 \\ -0.04 & 0.00 & -0.01 & 0.97 & 0.10 & -0.06 & -0.27 \\ 0.01 & 0.04 & 0.00 & 0.03 & 0.99 & -0.05 & -0.03 \\ -0.13 & -0.05 & -0.04 & -0.16 & 0.12 & 0.99 & 0.62 \\ -0.08 & 0.12 & -0.03 & 0.00 & -0.07 & 0.03 & 0.83 \end{bmatrix}$	$\begin{bmatrix} 0.99 & 0.02 & -0.00 & 0.01 & -0.09 & -0.01 & 0.13 \\ 0.05 & 0.85 & 0.01 & -0.07 & -0.28 & 0.01 & -0.01 \\ -0.06 & 0.15 & 0.98 & 0.04 & -0.25 & 0.00 & 0.02 \\ -0.10 & -0.06 & -0.03 & 0.88 & 0.13 & -0.09 & -0.27 \\ 0.08 & 0.04 & 0.03 & 0.11 & 1.07 & -0.04 & -0.12 \\ -0.14 & -0.02 & -0.05 & -0.15 & 0.23 & 1.03 & 0.51 \\ -0.13 & 0.22 & -0.04 & 0.02 & -0.07 & 0.03 & 0.87 \end{bmatrix}$
С	$\begin{bmatrix} 0.02 & 0.01 & -0.01 & -0.03 & -0.01 & 0.07 & -0.03 \end{bmatrix}^T$	$[0.01 \ 0.01 \ -0.01 \ -0.03 \ -0.01 \ 0.05 \ -0.03]^T$
S	$\begin{bmatrix} -0.01 & 0.09 & -0.10 & -0.02 & 0.00 & -0.02 & -0.20 \end{bmatrix}^T$	$\begin{bmatrix} 0.00 & 0.01 & -0.01 & 0.00 & 0.00 & 0.00 & -0.02 \end{bmatrix}^T$
t	0	$\begin{bmatrix} 0.01 & 0.00 & -0.02 & 0.00 & 0.00 & 0.00 \end{bmatrix}^T$
σ	0.851	0.957
$\delta$	-0.003	0.008





the responses at two test points in the region of interest by Sonnet's em (•): the coarse model (---), the enhanced coarse model (—)







the errors of the coarse model responses at the test points







the errors of the enhanced coarse model responses at the test points







#### **Microstrip Shaped T-Junction Optimization**

the enhanced coarse model is utilized

the optimization variables are X and Y

W = 24 mil, H = 25 mil and

specifications  $\varepsilon_r = 9.9$ 

 $|S_{11}| \le 1/3$ ,  $|S_{22}| \le 1/3$  in the frequency range 2 GHz to 20 GHz

OSA90/hope minimax optimization reached

X = 4.31 mil and Y = 19.77 mil





#### **Microstrip Shaped T-Junction Optimization**

optimum responses by Sonnet's *em* (•): the coarse model (---), the enhanced coarse model (—)







# Conclusions

we introduce a comprehensive framework called Generalized Space mapping (GSM) to engineering device modeling

in GSM we utilize a few relevant full-wave EM simulations to match the responses of the fine and coarse model over a designable region of parameters and frequency

GSM generalizes the Space Mapping (SM), the Frequency Space Mapping (FSM) and the Multiple Space Mapping (MSM) concepts to build a new engineering device modeling framework

two fundamental concepts are presented: Space Mapping Super Model (SMSM) and Frequency-Space Mapping Super Model (FSMSM)

MSM can be combined with SMSM and FSMSM to provide a powerful and reliable modeling tool for microwave devices